

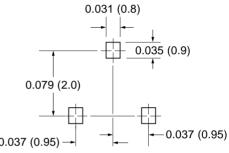
Dimensions in inches and (millimeters)

Features

- PNP Silicon Epitaxial Planar Transistors for switching and AF amplifier applications.
- Suited for low level, low noise, low frequency applications in hybrid circuits.
- · Low current, low voltage.
- As complementary types, BCX70 Series NPN transistors are recommended.

Mounting Pad Layout

BCX71 Series



Mechanical Data

Case: SOT-23 Plastic Package

Weight: approx. 0.008g

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Marking	BCX71G = BG	
Code:	BCX71H = BH	
	BCX71J = BJ	
	BCX71K = BK	

Packaging Codes/Options:

E8/10K per 13" reel (8mm tape), 30K/box E9/3K per 7" reel (8mm tape), 30K/box

Maximum Ratings & Thermal Characteristics Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	Value	Unit V	
Collector-Base Voltage	–Vcbo	45		
Collector-Emitter Voltage	-Vceo	45	V	
Emitter-Base Voltage	-Vево	5.0	V	
Collector Current	-lc	200	mA	
Peak Base Current	-l _B	50	mA	
Power Dissipation	Ptot	250	mW	
Thermal Resistance Junction to Ambient Air	Røja	500 ⁽¹⁾	°C/W	
Junction Temperature	Tj	150	۵°	
Storage Temperature Range	Tstg	-65 to +150	°C	

Note: (1) Mounted on FR-4 printed-circuit board.

BCX71 Series

Vishay Semiconductors formerly General Semiconductor



Electrical Characteristics (TJ = 25°C unless otherwise noted)

Parameter		Symbol	Test Condition	Min	Тур	Max	Unit
DC Current Gain	BCX71G BCX71H BCX71J BCX71K BCX71G BCX71H BCX71J BCX71K BCX71G BCX71H BCX71J BCX71J	hFE	$\begin{array}{c} -VCE = 5 \ V, -IC = 10 \ \mu A \\ -VCE = 5 \ V, -IC = 10 \ \mu A \\ -VCE = 5 \ V, -IC = 10 \ \mu A \\ -VCE = 5 \ V, -IC = 10 \ \mu A \\ -VCE = 5 \ V, -IC = 2 \ m A \\ -VCE = 5 \ V, -IC = 2 \ m A \\ -VCE = 5 \ V, -IC = 2 \ m A \\ -VCE = 5 \ V, -IC = 2 \ m A \\ -VCE = 5 \ V, -IC = 2 \ m A \\ -VCE = 1 \ V, -IC = 50 \ m A \\ -VCE = 1 \ V, -IC = 1 \ V, -IC = 50 \ m A \\ -VCE = 1 \ V, -IC = 1 \ V, $				
Collector-Emitter Saturation Vo	oltage	-VCEsat	-Ic = 10 mA, -I _B = 0.25 mA -Ic = 50 mA, -I _B = 1.25 mA	60 120		250 550	mV
Base-Emitter Saturation Voltag	e	-VBEsat	-IC = 10 mA, -I _B = 0.25 mA -IC = 50 mA, -I _B = 1.25 mA	600 680	—	850 1050	mV
Base-Emitter Voltage		–Vbe	$\label{eq:VCE} \begin{array}{l} -V_{CE} = 5 \ V, -I_{C} = 2 \ mA \\ -V_{CE} = 5 \ V, -I_{C} = 10 \ \mu A \\ -V_{CE} = 1 \ V, -I_{C} = 50 \ mA \end{array}$	600 — —	650 550 720	750 — —	mV
Collector Cut-off Current		-Ісво	-V _{CB} = 45 V, V _{EB} = 0 -V _{CB} = 45 V, V _{EB} = 0 T _A = 150°C		_	20 20	nA μA
Emitter Cut-off Current		-I _{EBO}	$-V_{EB} = 4 \text{ V}, \text{ IC} = 0$		—	20	nA
Gain-Bandwidth Product		fт	-VCE = 5 V, -IC = 10 mA f = 100 MHz	100	_	_	MHz
Collector-Base Capacitance		Ссво	$-V_{CB} = 10 \text{ V}, \text{ f} = 1 \text{ MHz}, \text{ IE} = 0$		4.5		pF
Emitter-Base Capacitance		Сево	$-V_{CB} = 0.5 V$, f = 1 MHz, IC = 0		11	—	pF
Noise Figure		F	$\label{eq:VCE} \begin{split} -V_{CE} &= 5 \text{ V}, -I_{C} = 200 \ \mu\text{A}, \\ \text{Rs} &= 2 \ \text{k}\Omega, \ \text{f} = 100 \ \text{kHz}, \\ \text{B} &= 200 \ \text{Hz} \end{split}$	_	2	6	dB
Small Signal Current Gain	BCX71G BCX71H BCX71J BCX71K	hfe	-Vce = 5 V, -Ic = 2 mA, f = 1.0 kHZ		200 260 330 520		
Turn-on Time at $R_L = 990\Omega$ (se	ee fig. 1)	ton	$-V_{CC} = 10 \text{ V}, -I_C = 10 \text{ mA},$ $-I_{B(on)} = I_{B(off)} = 1 \text{ mA}$	_	85	150	ns
Turn-off Time at $R_L = 990\Omega$ (se	ee fig. 1)	toff	$-V_{CC} = 10 \text{ V}, -I_{C} = 10 \text{ mA},$ $-I_{B(on)} = I_{B(off)} = 1 \text{ mA}$	_	480	800	ns



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Ratings and Characteristic Curves (TA = 25°C unless otherwise noted)

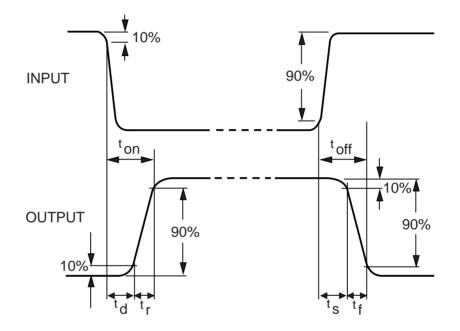


Fig. 1 Switching Waveforms